



YOUSHANG SEMICONDUCTOR

设计研发新型功率器件

各类小信号开关

中低压及高压大电流等场效应管

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Description

This bipolar junction transistor (BJT) is designed to meet the stringent requirement of automotive applications.

Features

- $BV_{CEO} > -140V$
- $I_C = -3A$ Continuous Collector Current
- $I_{CM} = -10A$ Peak Pulse Current
- Very Low Saturation Voltage
- $R_{SAT} = 85m\Omega @ I_C -3A$ for Low Equivalent On-Resistance

Mechanical Data

- Case: SOT89
- Case Material: Molded Plastic. "Green" Molding Compound. UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish — Matte Tin Plated Leads. Solderable per MIL-STD-202, Method 208 
- Weight: 0.05 grams (Approximate)

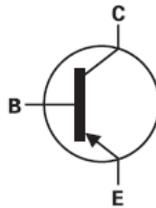
Applications

- Motor Driving
- Line Switching
- High Side Switches
- Subscriber Line Interface Cards (SLIC)

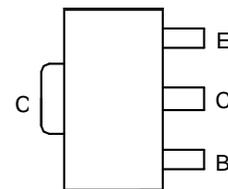
SOT89



Top View



Device Schematic



Pin-Out Top View

Absolute Maximum Ratings (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	-180	V
Collector-Emitter Voltage	V_{CEO}	-140	V
Emitter-Base Voltage	V_{EBO}	-7	V
Continuous Collector Current	I_C	-3	A
Peak Pulse Current	I_{CM}	-10	A

Thermal Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

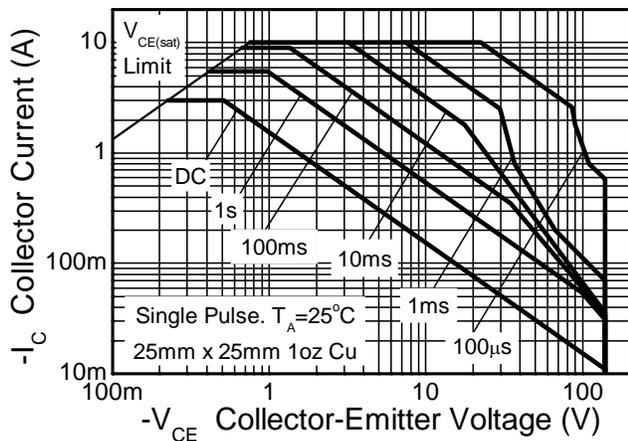
Characteristic		Symbol	Value	Unit
Power Dissipation Linear Derating Factor	(Note 5)	P_D	1.5	W
	(Note 6)		12	
Thermal Resistance, Junction to Ambient	(Note 5)	$R_{\theta JA}$	2.1	$^\circ\text{C/W}$
	(Note 6)		16.8	
Operating and Storage Temperature Range	(Note 5)	T_J, T_{STG}	83	$^\circ\text{C}$
	(Note 6)		60	
			-55 to +150	

ESD Ratings (Note 7)

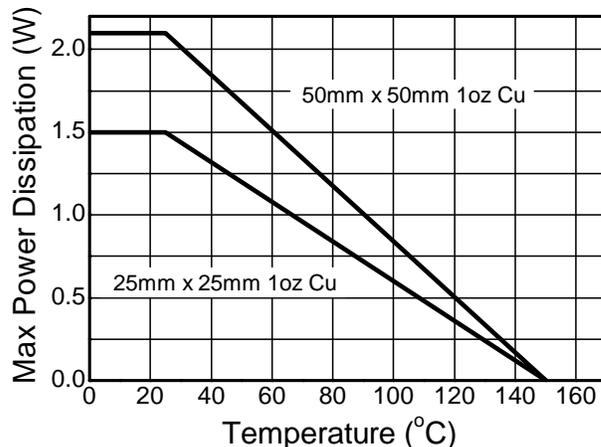
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge — Human Body Model	ESD HBM	4000	V	3A
Electrostatic Discharge — Machine Model	ESD MM	400	V	C

- Notes:
- For a device mounted with the collector lead on 25mm x 25mm 1oz copper that is on a single-sided 1.6mm FR-4 PCB; device is measured under still air conditions whilst operating in steady-state.
 - Same as Note 5, except the device is mounted on 50mm x 50mm 1oz copper.
 - Refer to JEDEC specification JESD22-A114 and JESD22-A115.

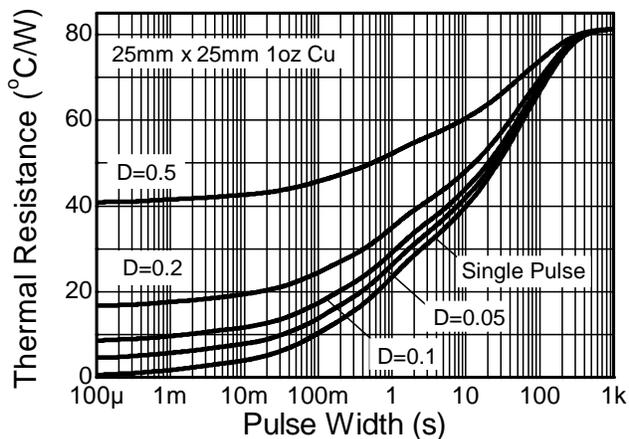
Thermal Characteristics and Derating Information



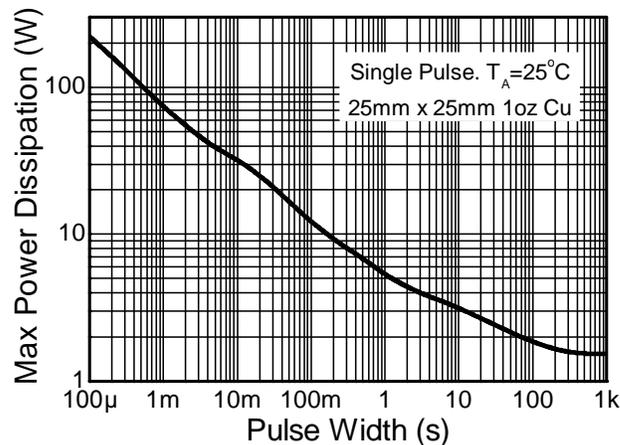
Safe Operating Area



Derating Curve



Transient Thermal Impedance



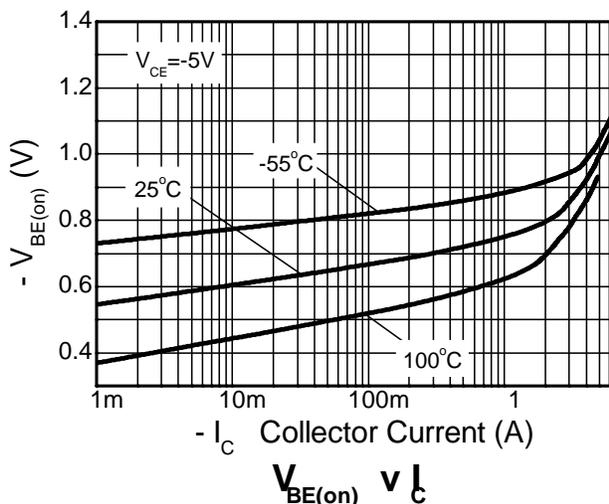
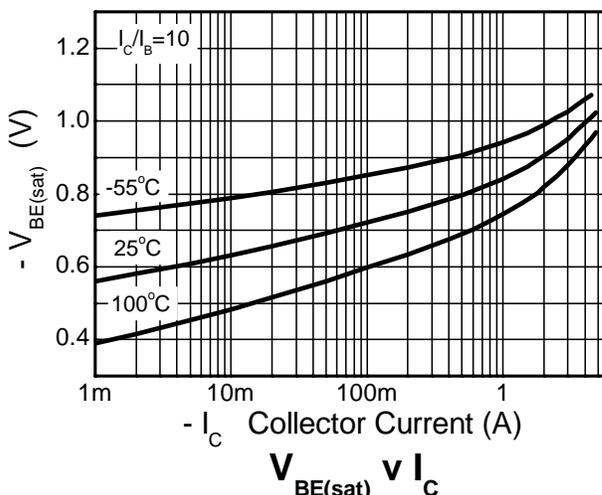
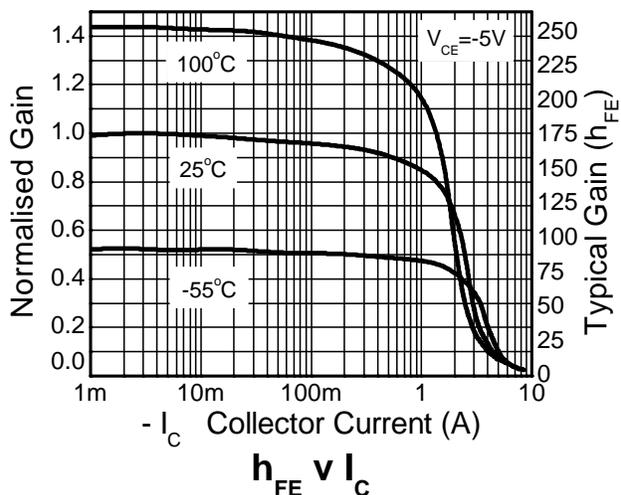
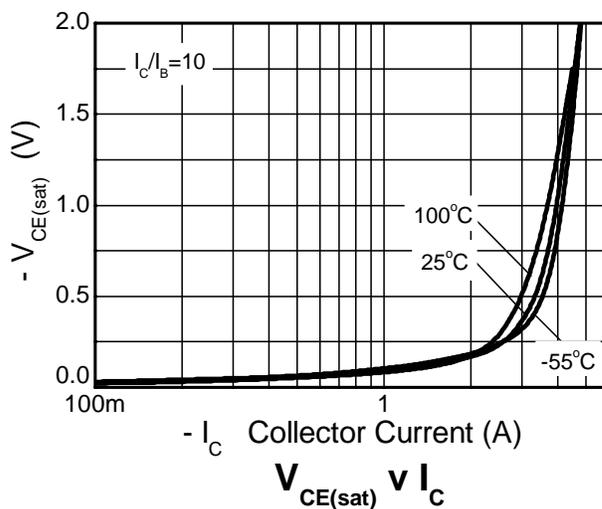
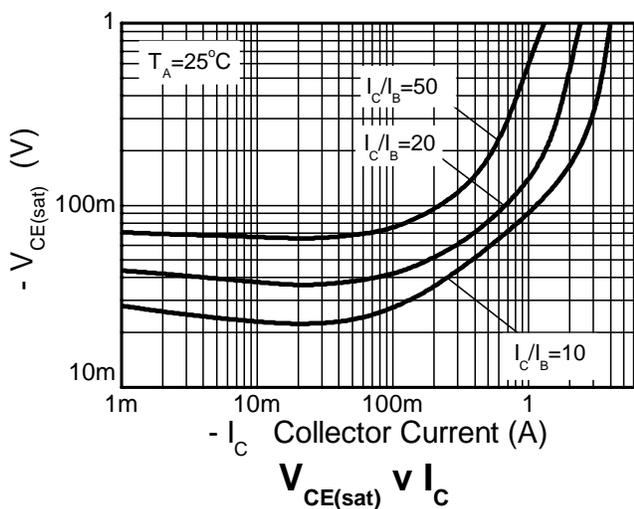
Pulse Power Dissipation

Electrical Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

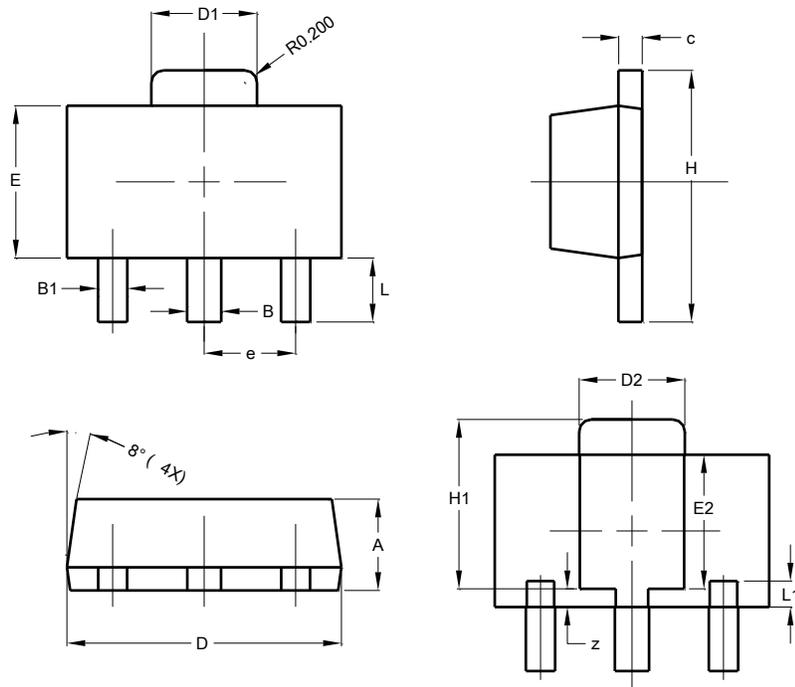
Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV_{CBO}	-180	-200	—	V	$I_C = -100\mu\text{A}$
Collector-Emitter Breakdown Voltage	BV_{CER}	-180	-200	—	V	$I_C = -1\mu\text{A}$, $R_B \leq 1\text{k}\Omega$
Collector-Emitter Breakdown Voltage (Note 8)	BV_{CEO}	-140	-160	—	V	$I_C = -10\text{mA}$
Emitter-Base Breakdown Voltage	BV_{EBO}	-7.0	-8.0	—	V	$I_E = -100\mu\text{A}$
Collector Cutoff Current	I_{CBO}	—	< -1	-20	nA	$V_{CB} = -150\text{V}$
Collector Cutoff Current	I_{CER} $R \leq 1\text{k}\Omega$	—	< -1	-20	nA	$V_{CB} = -150\text{V}$
Emitter Cutoff Current	I_{EBO}	—	< -1	-10	nA	$V_{CB} = -150\text{V}$, $T_A = +100^\circ\text{C}$
Collector-Emitter Saturation Voltage (Note 8)	$V_{CE(sat)}$	—	-37 -50 -80 -255	-60 -75 -115 -330	mV	$I_C = -0.1\text{A}$, $I_B = -5\text{mA}$ $I_C = -0.5\text{A}$, $I_B = -50\text{mA}$ $I_C = -1\text{A}$, $I_B = -100\text{mA}$ $I_C = -3\text{A}$, $I_B = -300\text{mA}$
Base-Emitter Saturation Voltage (Note 8)	$V_{BE(sat)}$	—	-910	-1010	mV	$I_C = -3\text{A}$, $I_B = -300\text{mA}$
Base-Emitter Turn-On Voltage (Note 8)	$V_{BE(on)}$	—	-800	-900	mV	$I_C = -3\text{A}$, $V_{CE} = -5\text{V}$
DC Current Gain (Note 8)	h_{FE}	100 100 45 —	225 200 100 5	— 300 — —	—	$I_C = -10\text{mA}$, $V_{CE} = -5\text{V}$ $I_C = -1\text{A}$, $V_{CE} = -5\text{V}$ $I_C = -3\text{A}$, $V_{CE} = -5\text{V}$ $I_C = -10\text{A}$, $V_{CE} = -5\text{V}$
Transition Frequency	f_T	—	120	—	MHz	$V_{CE} = -10\text{V}$, $I_C = -100\text{mA}$, $f = 50\text{MHz}$
Output Capacitance	C_{OBO}	—	33	—	pF	$V_{CB} = -10\text{V}$, $f = 1\text{MHz}$
Switching Time	t_{ON}	—	42	—	ns	$V_{CC} = -50\text{V}$, $I_C = -1\text{A}$, $I_{B1} = -I_{B2} = -100\text{mA}$
	t_{OFF}	—	636	—		

 Note: 8. Measured under pulsed conditions. Pulse width $\leq 300\mu\text{s}$. Duty cycle $\leq 2\%$.

Typical Electrical Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

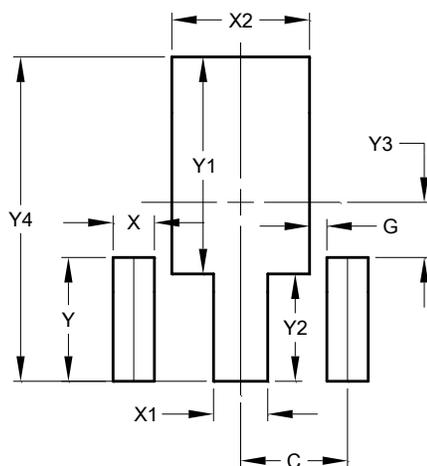


Package Outline Dimensions

SOT89


SOT89			
Dim	Min	Max	Typ
A	1.40	1.60	1.50
B	0.50	0.62	0.56
B1	0.42	0.54	0.48
c	0.35	0.43	0.38
D	4.40	4.60	4.50
D1	1.62	1.83	1.733
D2	1.61	1.81	1.71
E	2.40	2.60	2.50
E2	2.05	2.35	2.20
e	-	-	1.50
H	3.95	4.25	4.10
H1	2.63	2.93	2.78
L	0.90	1.20	1.05
L1	0.327	0.527	0.427
z	0.20	0.40	0.30
All Dimensions in mm			

Suggested Pad Layout

SOT89


Dimensions	Value (in mm)
C	1.500
G	0.244
X	0.580
X1	0.760
X2	1.933
Y	1.730
Y1	3.030
Y2	1.500
Y3	0.770
Y4	4.530